Please delete and replace the paragraph at **page 8, lines 13 to 14**, to read as follows:

B2 Figs. 6A, 6B and 6C illustrate the oxygen pressure dependency of transmittance of the IDIXO film having a thickness of 120 nm, by showing the transmittance characteristic at three different pressures;

Please delete and replace the paragraph at **page 8, lines 15 to 16**, to read as follows:

B3 Figs. 7A, 7B and 7C illustrate the dependency of transmittance of IDIXO (120 nm)/Au with respect to the film thickness of the Au film by showing the transmittance characteristic at three different Au film thicknesses.

Please delete and replace the paragraph at **page 8, lines 27 to 31**, to read as follows:

B4 In a first embodiment of the present invention, a transparent conductor film having low resistance and high transmittance is employed in place of a conventional Au film. Referring to Fig. 1A, the transparent conductor film is applied as a p-type electrode in the first embodiment of the present invention in particular.

Please delete and replace the paragraph at **page 8, line 32 to page 9, line 3**, to read as follows:

B5

Referring to comparative Fig. 1C, a transparent conductor film 30 generally consists of an n-type semiconductor, and inevitably forms a junction when directly formed on a p-type semiconductor layer 24. Referring to comparative Fig. 1B, transmittance as well as luminous efficiency are reduced when a relatively thick Au film 26 is formed on a p-type semiconductor layer 24.

Please delete and replace the paragraph at **page 9, lines 4 to 11**, to read as follows:

B6

Referring to Fig. 1D, an extremely thin Au thin film 10a is formed on a p-type semiconductor layer 24, and a transparent conductor film 10b is thereafter stacked thereon according to the present invention. The Au thin film 10a has a sufficiently small thickness of 1 to 3 nm, so that the transmittance is not remarkably reduced. The transparent conductor film 10b having high transmittance can be formed with a relatively large thickness. Consequently, a current effectively spreads over an electrode through the transparent conductor film 10b.

Please delete and replace the paragraph at **page 14, lines 15 to 23**, to read as follows:

B7

Figs. 6A, 6B and 6C show results of evaluation of the oxygen pressure dependency of transmittance of IDIXO films on substrates of MgO, respectively for three different film

forming oxygen pressures. An absorption edge of about 300 nm is recognized. The sample for measuring transmittance was formed by a substrate of MgO having an absorption edge of about 200 nm, and it is understood that absorption of 300 nm results from the IDIXO film. The transmittance of the MgO substrate measured at a wavelength of 500 nm was 84%, and the relation between the film forming oxygen pressure and the transmittance of the IDIXO film (120 nm) can be calculated as shown in Table 3.

B7

Please delete and replace Table 3 at **page 14, lines 25 to 30**, to read as follows:

Table 3

B8

Film Forming Oxygen Pressure	IDIXO Transmittance
0.3 Torr	99%
$3x10^{-2}$ Torr	87%
$3x10^{-3}$ Torr	92%

Please delete and replace the paragraph at **page 17, lines 16 to 22**, to read as follows:

B9

Figs. 7A, 7B and 7C show transmittance in IDIXO/Au electrode structures having three different film thicknesses of the Au film, respectively. Reduction of transmittance resulting from the presence of Au is recognized. At a wavelength of 500 nm, the transmittance of the sample of IDIXO (120 nm)/Au (3 nm) is about 80%.